

Note on C-DLTS application for study of radiation damage produced by short range particles. V. Eremin, D. Mitina, E. Verbitskaya

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Short range particles like alphas, low energy protons, ions, etc. are cost effective approaches for the damage production in silicon. The physics of capacitance DLTS application for study of such structures is discussed. The approach is illustrated by the results on silicon detectors irradiated by heavy ions.

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